Inelastic current-voltage characteristics of atom ic and m olecular junctions

Yu-Chang Chen

Department of Physics, University of California, San Diego, La Jolla, CA 92093-0319

Michael Zwolak

Department of Physics, California Institue of Technology, Pasadena, California 91125

Massimiliano Di Ventra [*]

Department of Physics, University of California, San Diego, La Jolla, CA 92093-0319

We report rst-principles calculations of the inelastic current-voltage (I-V) characteristics of a gold point contact and a molecular junction in the nonresonant regime. Discontinuities in the I-V curves appear in correspondence to the normal modes of the structures. Due to the quasi-onedimensional nature of these systems, speci c modes with large longitudinal component dom inate the inelastic I-V curves. In the case of the gold point contact, our results are in good agreement with recent experimental data. For the molecular junction, we not that the inelastic I-V curves are quite sensitive to the structure of the contact between the molecular and the electrodes thus providing a pow erful tool to extract the bonding geometry in molecular wires.

Inelastic scattering between electrons and phonons in a current-carrying wire is a source of energy dissipation for electrons. How ever, it can also yield a lot of inform ation on the underlying atom ic structure of the wire. This inform ation can be extracted indirectly from the discontinuities in conductance that occur when the external bias is large enough to excite discrete vibrationalm odes of the wire. [1] Recent experiments on transport properties of atom ic [2] and m olecular [3, 4] junctions have indeed revealed such inelastic features. It is, how ever, not straightforward to relate these features to speci c vibrational m odes. A nanoscale junction (often described as a quasione-dimensional system) with N atom s supports 3N vibrational modes. In a strictly one-dimensional system, only longitudinal modes can be excited via electronic coupling. However, the modes of a realistic junction are not necessarily purely transverse or purely longitudinal with respect to the direction of current ow. , 6, 7] Therefore, the inelastic current-voltage (I-V) characteristics are likely to depend strongly on the detailed atom ic structure of the full system . This is particularly relevant for molecular junctions for which the contact geometry between the molecule and the bulk electrodes is di cult to control in experim ents. [8, 9]

In this letter we rst derive an expression for the inelastic current in a current-carrying system in terms of scattering wavefunctions. This expression allows us to study the inelastic I-V characteristics of a given nanoscale junction using rst-principles approaches. As an example we study the e ect of vibrations on the electron dynamics in a gold point contact and a single-molecule junction. For the gold point contact, the magnitude of the calculated inelastic current as well as its onset compare very well with recent experimental results. [2] For the molecular junction, we analyze the case in which the molecule is equally bonded to the two bulk electrodes and the case in which the two contacts are di erent. We nd that the inelastic I-V characteristics are very di erent in the two cases. This result shows that inelastic spectroscopy could be used quite e ectively to extract inform ation on the contact geom etry of molecular wires.

Let us start by deriving an expression for the inelastic current. We assume that the phonon distribution is at equilibrium at all (sm all) biases, thus neglecting localheating. [5] We have previously shown that for sm all biases this e ect is sm all, provided good therm al contacts exist between the nanostructures and the bulk electrodes. [5] The many-body Ham iltonian of the system is (atom ic units are used throughout this paper) [5]

$$H = H_{el} + H_{vib} + H_{el vib}; \qquad (1)$$

where $H_{el} \stackrel{i}{_{p}}$ is the electropic part of the Ham iltonian; $H_{vib} = \frac{1}{2} \qquad q_{4}^{2} + \frac{1}{2} \qquad !_{i}^{2} q_{i}^{2}$ is the ionic contri $i_{i, 2vib}$ bution where q_{i} is the norm all coordinate and $!_{i}$ is the norm all frequency corresponding to the i-th ion and th component; nally, $H_{el \ vib}$ describes the electron-ion interaction and has the following form:

$$H_{el vib} = \begin{matrix} X & X & X \\ s & \vdots & E_{1}; E_{2}i; j 2vib \\ s & \frac{\tilde{z}}{2!j} A_{i}; j & J_{E_{1}; E_{2}}^{i} a_{E_{1}}^{y} a_{E_{2}} & b_{j} + b_{j}^{y} ; (2) \end{matrix}$$

where $= L; R; a_E$ and b_j are the electron and phonon annihilation operators, respectively, satisfying the usual commutation relations. $A_i;_j$ are the matrix elements of the transform ation from cartesian coordinates to normal coordinates, and J_{E_1,E_2}^{i} is the electron-phonon coupling constant which can be directly calculated from the scattering wave-functions [5]

 $J_{E_{1};E_{2}}^{i} = dr dK_{k} E_{1} r; K_{k} @ V^{ps}(r; R_{i}) E_{2} r; K_{k};$ (3)

where we have chosen to describe the electron-ion interaction with pseudopotentials V $^{\rm ps}$ (r;R $_{\rm i})$ for each i-th ion. [10]

Similar to what has been done in Ref. 6, we treat the electron-phonon interaction to st-order perturbation theory. [11] Due to the orthogonality condition between phonon states, higher harm onics for each phonon mode appear only in third-order perturbation theory and are therefore sm all. [12] W e develop the full m anybody wavefunctions in term softhe states $\begin{bmatrix} L & (R) \\ E \end{bmatrix}$; $n_j = D$ L(R) hn_j j. The single-particle electronic state is described by ${}^{\rm L\ (R\)}_{\rm E}$ r;K $_{\rm k}$, corresponding to electrons incident from the left (right) electrodes with energy E and m om entum K $_{k}$ parallel to the electrode surface. [10] These electronic states are calculated self-consistently by means of a scattering approach within the density functional theory of many-electron system s. [10] The phonon state is described by $\ln_i j$ where n_i is the number of phonons in the j -th norm alm ode.

$$j_{E};n_{j} i = \lim_{\substack{! 0^{+} \\ 0^{+} \\ 0^{+} \\ 0^{-}$$

In the above expression D_E is the partial density of states corresponding to the current-carrying states and "(E;n_j) = E + (n_j + 1=2)~!_j is the energy of state j_E;n_j i. We have also assumed that the electrons rapidly them alize into the bulk electrodes so that their statistics are given by the equilibrium Ferm i-D irac distribution, $f_E^{L(R)} = 1 = (\exp[(E - E_{FL(R)})] = k_B T_e] + 1)$ with chem ical potential $E_{FL(R)}$ deep into the left (right) electrode. [13] U sing lim $! 0 \frac{1}{z i} = P(\frac{1}{z}) + i$ (z), the rst-order correction j_E; n_j i assumes the following form :

where $m_j i = 1 = [exp(]_j = k_B T_w)$ 1] is the Bose-E instein distribution per mode at a given wire tem perature T_w , and hi indicates the statistical average. The above expression allows us to calculate the inelastic current. It is evident from Eq.5 that for a xed partial density of states, the magnitude of the inelastic current is determ ined by the coupling constant $J_{E_{\,1}\,;E_{\,2}}^{\text{i}}$ and the transform ation matrix $A = fA_{i}$; g which contains the inform ation on the geom etry of the structure and hence on the character (transverse versus longitudinal) of the di erent modes. [4] W e will be concerned with the extra inelastic current due to the vibrationalm odes of the atom s of the nanoscale constriction with respect to the continuum spectrum ofmodes of the bulk electrodes. [15] If the electronic tem perature T_e is zero, then, for an external bias V, only those norm alm odes with eigenener $gies \sim !_{i} < eV$ can be excited and contribute to Eq.5. In addition, due to our assumption of negligible local heating, the averaged number of phonons \ln_1 i is zero for all norm alm odes. In this case the st-order correction to the current induced by electron-phonon interaction assum es the follow ing sim ple form :

$$I = i \qquad dE \qquad dR \qquad dK_{k}$$

$$I = E_{FL}$$

$$\left[\begin{array}{ccc} R \\ E \\ E \end{array} \right] \left[\begin{array}{ccc} R \\ E \\ E \end{array} \right] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \\ E \end{array} \right] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \end{array} \left] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \end{array} \left] \left[\begin{array}{ccc} R \end{array} \right] \left[\begin{array}{ccc} R \end{array} \right] \left[\left[\begin{array}{ccc} R \end{array} \right]$$

where only the left-travelling electronic states contribute (if the left electrode is positively biased).

W e are now ready to use the above expression to study inelastic scattering in speci c system s. W e choose to rst study a gold point contact for which experim ental results are available [2] and then discuss the case of a molecular junction. In Fig. 1 we plot the inelastic conductance for a single gold atom.

In the absence of inelastic scattering and for the bias range of Fig. 1, the I-V characteristics of this system are linear with di erential conductance G ' 1:1 G₀, where $G_0 = 2e^2=h$. [5] W hen electron-phonon interactions are considered, two transverse modes with energy ~! ' 10:8 m eV are rst excited with increasing bias. How ever, due to their transverse character, these modes contribute negligibly to the inelastic current as determined by the

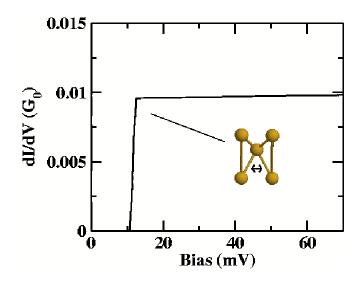


FIG.1: A bsolute value of the di erential conductance due to electron-phonon interaction as a function of bias for a gold point contact. Two norm almodes corresponding to transverse vibration of the gold atom between the electrodes have energies of 10.8 m eV, which are close in energy to the longitudinalmode at 11.5 m eV (shown in the gure).

product between the transform ation matrix A and the coupling constant $J_{E_1;E_2}^{i}$. An abrupt change in di erential conductance appears at V ' 11.5 m V corresponding to the excitation of a longitudinal vibrationalm ode (see schem atic in Fig. 1). [16] Both the onset bias as well as the change in conductance (of about 1%) are in good agreem ent with experim ental reports on gold point contacts. [2] The longitudinal and transverse modes are very close in energy but mainly the longitudinal mode contributes to the inelastic current, [6, 7] so that in experiments the transverse ones would not be easily resolved. This is even more evident in the case of the molecular junction.

In Fig. 2 we plot the inelastic conductance in the case in which a phenyldithiolate molecule forms symmetric contacts on both sides of the junction, i.e., each S atom is bonded to a at surface. In this case there is a total of 14 m odes with energy less than 100 m eV. A prom inent change in conductance occurs at a bias of about 18 m V, i.e., at a bias large enough to excite two modes with large longitudinal component (see Fig. 2). [17] The inelastic contribution from two transverse modes at lower bias [5] is alm ost four orders of m agnitude sm aller. Sim ilarly, three quasi-transverse modes with energies between 20 and 50 m eV contribute negligibly to the inelastic conductance. They only appear as sm all features in the second derivative of the current with respect to the bias (see Fig. 2). [18] It is likely that due to noise and other effects, such m odes would not be resolved in experim ents. Increasing the bias further, a second large step in the absolute value of the conductance is found at about 50 mV (see Fig. 2). This again corresponds to a predom i-

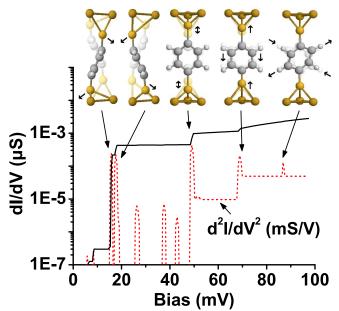


FIG.2: A bsolute value of the di erential conductance due to electron-phonon interaction as a function of bias for a sym m etric molecular junction. The derivative of the conductance with respect to bias is also shown (a broadening of 1 m eV is introduced). The schem atics show only the modes that contribute the most to the inelastic current.

nantly longitudinalm ode (see schem atic in Fig.2). This m ode is then followed by others that have both a transverse and a longitudinal component. The magnitude of the conductance steps depends on the relative amount of the two components as well as the product between the transform ation matrix A and the coupling constant. [17]

W e conclude by showing how sensitive the inelastic current is to any change in the bonding properties of the molecule to the electrodes. W e illustrate this in Fig. 3 where we plot the inelastic conductance for the same molecule but with one of the S atoms bonded to a H atom which, in turn, is not bonded to the nearby surface (see schematics in Fig. 3). [19] Such a con guration could be easily realized in experiments. [8] In the present case there are 13 m odes below 100 m eV, of which only six have large longitudinal component (shown in Fig. 3) [17] and contribute to small steps in the inelastic conductance, with the one at about 11 m eV showing the largest relative contribution. All other modes contribute negligibly to the current. Comparing Figs. 2 and 3 it is clear that contact geom etry a ects considerably the I-V characteristics of the system both in the position of the inelastic discontinuities as well as in their relative m aqnitude. This fact, however, can be used advantageously to extract a posteriori the contact structure ofm olecular junctions thus providing a powerful diagnostic tool for nanoscale electronics.

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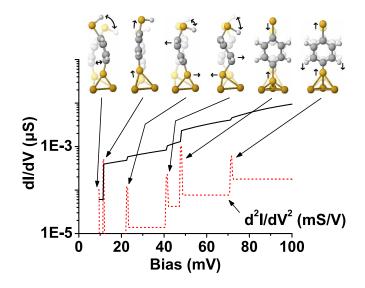


FIG. 3: A bsolute value of the di erential conductance due to electron-phonon interaction as a function of bias for a m olecular junction with asym m etric contacts. The derivative of the conductance with respect to bias is also shown (a broadening of 1 m eV is introduced). The schem atics show only the m odes that contribute the m ost to the inelastic current.

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- * E-m ail address: diventra@ physics.ucsd.edu
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- ¹⁴ A quantitative way of distinguishing between longitudinal versus transverse character of each mode is to sum up the absolute values of all the z-component (i.e., along the current ow) matrix elements of A.
- $^{\rm 15}$ W e have employed H artree-Fock total energy calculations [see, e.g., J.A. Boatz and M.S. Gordon, JPhys. Chem., 93, 1819 (1989)] to evaluate the vibrationalm odes of the single-m olecule junctions and the gold point contact. For these calculations, the assum ed surface orientation is [111] represented by a triangular pad of gold atom s with in nite m ass (see insets of Figs. 1 and 2). The structures were relaxed starting from an initial geometry where the single gold atom of the point contact faces the center of the triangular pad at a distance of 2.3A; and for the single-m olecule junction with symmetric contacts the initial S-surface distance is 2.4A. In the case of asymmetric contacts the S atom on one side of the junction is bonded to a H atom (see insets of Fig. 3). This thiol term ination is assumed to be far from the nearby surface so that the modes of this structure are not in uenced by the gold atom s of the surface.
- ¹⁶ N ote that the inelastic correction to the current is actually negative.For convenience we plot in this paper the absolute value of this correction.
- ¹⁷ In the molecular junction cases, the dominant net contribution to the electron-phonon coupling is from the S atom s and the adjacent C atom s (i.e., the two C atom s that form a straight line with the S atom s). This im plies that those modes that do not have large displacements of these atom s along the z direction will contribute negligibly to the inelastic current, even if the global character of the mode is longitudinal as inferred from the procedure outlined in R ef. 14. This is, e.g. the case for the mode at about 90 m eV shown schematically in Fig. 2.
- ¹⁸ A broadening of 1 m eV is introduced in all calculations to m ake the second derivative of the inelastic current as a function of bias nite at the conduction jumps.
- ¹⁹ In order to facilitate the com parison with the previous case, we have assumed in this calculation the same coupling constants, partial density of states and unperturbed current as for the symmetric junction case.